



# BUK9Y1R3-40H

N-channel 40 V, 1.3 mΩ logic level MOSFET in LFPAK56

31 May 2018

Product data sheet

## 1. General description

Automotive qualified N-channel MOSFET using the latest Trench 9 low ohmic superjunction technology, housed in a robust LFPAK56 package. This product has been fully designed and qualified to meet AEC-Q101 requirements delivering high performance and endurance.

## 2. Features and benefits

- Fully automotive qualified to AEC-Q101:
  - 175 °C rating suitable for thermally demanding environments
- Trench 9 Superjunction technology:
  - Reduced cell pitch enables enhanced power density and efficiency with lower  $R_{DSon}$  in same footprint
  - Improved SOA and avalanche capability compared to standard TrenchMOS
  - Tight  $V_{GS(th)}$  limits enable easy paralleling of MOSFETs
- LFPAK Gull Wing leads:
  - High Board Level Reliability absorbing mechanical stress during thermal cycling, unlike traditional QFN packages
  - Visual (AOI) soldering inspection, no need for expensive x-ray equipment
  - Easy solder wetting for good mechanical solder joint
- LFPAK copper clip technology:
  - Improved reliability, with reduced  $R_{th}$  and  $R_{DSon}$
  - Increases maximum current capability and improved current spreading

## 3. Applications

- 12 V automotive systems
- Motors, lamps and solenoid control
- Start-Stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

## 4. Quick reference data

Table 1. Quick reference data

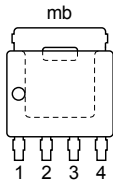
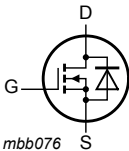
| Symbol    | Parameter               | Conditions  |     | Min | Typ | Max | Unit |
|-----------|-------------------------|---|-----|-----|-----|-----|------|
| $V_{DS}$  | drain-source voltage    | $25\text{ °C} \leq T_j \leq 175\text{ °C}$                            |     | -   | -   | 40  | V    |
| $I_D$     | drain current           | $V_{GS} = 10\text{ V}; T_{mb} = 25\text{ °C};$ <a href="#">Fig. 2</a> | [1] | -   | -   | 190 | A    |
| $P_{tot}$ | total power dissipation | $T_{mb} = 25\text{ °C};$ <a href="#">Fig. 1</a>                       |     | -   | -   | 395 | W    |

| Symbol                         | Parameter                        | Conditions   | Min  | Typ  | Max  | Unit |
|--------------------------------|----------------------------------|--|------|------|------|------|
| <b>Static characteristics</b>  |                                  |  |      |      |      |      |
| $R_{DS(on)}$                   | drain-source on-state resistance | $V_{GS} = 10\text{ V}$ ; $I_D = 25\text{ A}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 11</a>                              | 0.67 | 0.96 | 1.3  | mΩ   |
| <b>Dynamic characteristics</b> |                                  |  |      |      |      |      |
| $Q_{GD}$                       | gate-drain charge                | $I_D = 25\text{ A}$ ; $V_{DS} = 20\text{ V}$ ; $V_{GS} = 4.5\text{ V}$ ; <a href="#">Fig. 13</a> ; <a href="#">Fig. 14</a> | -    | 11.2 | 22.4 | nC   |
| <b>Source-drain diode</b>      |                                  |  |      |      |      |      |
| $Q_r$                          | recovered charge                 | $I_S = 25\text{ A}$ ; $di_S/dt = -100\text{ A}/\mu\text{s}$ ; $V_{GS} = 0\text{ V}$ ;                                      | -    | 38.8 | -    | nC   |
| S                              | softness factor                  | $V_{DS} = 20\text{ V}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 17</a>  | -    | 0.8  | -    |      |

[1] 190A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature

## 5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description                       | Simplified outline  | Graphic symbol  |
|-----|--------|-----------------------------------|---|---|
| 1   | S      | source                            |  <p>LFAK56; Power-SO8 (SOT669)</p> |  <p>mbb076 S</p> |
| 2   | S      | source                            |   |   |
| 3   | S      | source                            |   |   |
| 4   | G      | gate                              |   |   |
| mb  | D      | mounting base; connected to drain |   |   |

## 6. Ordering information

Table 3. Ordering information

| Type number  | Package           |  |         |
|--------------|-------------------|--|---------|
|              | Name              | Description  | Version |
| BUK9Y1R3-40H | LFAK56; Power-SO8 | plastic, single-ended surface-mounted package; 4 terminals | SOT669  |

## 7. Marking

Table 4. Marking codes

| Type number  | Marking code |
|--------------|--------------|
| BUK9Y1R3-40H | 91H340       |

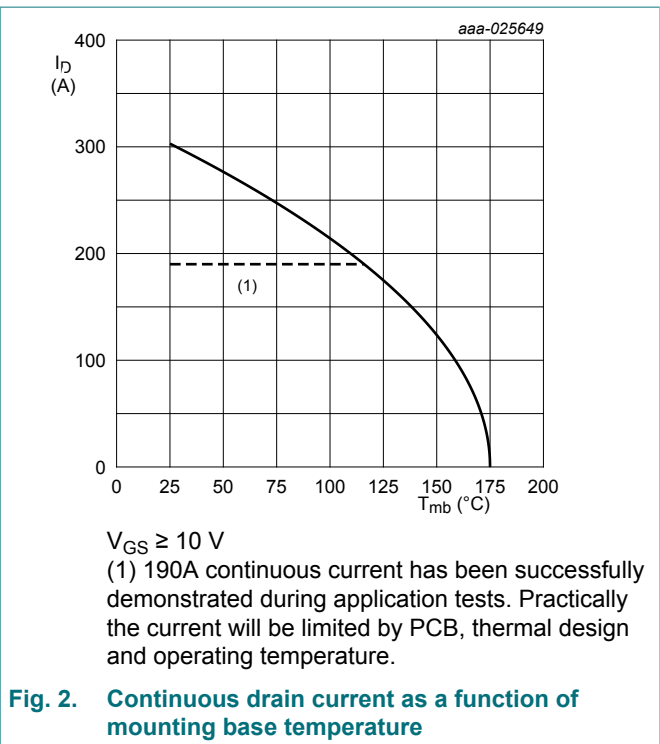
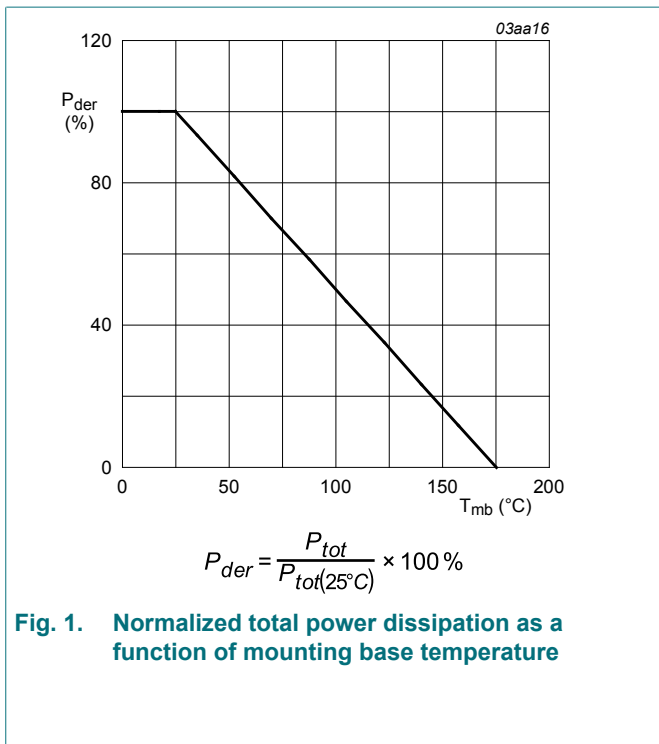
## 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol                      | Parameter                                    | Conditions   |         | Min | Max | Unit |
|-----------------------------|--|--|---------|-----|-----|------|
| V <sub>DS</sub>             | drain-source voltage                         | 25 °C ≤ T <sub>j</sub> ≤ 175 °C  |         | -   | 40  | V    |
| V <sub>GS</sub>             | gate-source voltage                          | DC; T <sub>j</sub> ≤ 175 °C  |         | -10 | 16  | V    |
| P <sub>tot</sub>            | total power dissipation                      | T <sub>mb</sub> = 25 °C; Fig. 1  |         | -   | 395 | W    |
| I <sub>D</sub>              | drain current                                | V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; Fig. 2  | [1]     | -   | 190 | A    |
|                             |  | V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; Fig. 2   | [1]     | -   | 190 | A    |
| I <sub>DM</sub>             | peak drain current                           | pulsed; t <sub>p</sub> ≤ 10 μs; T <sub>mb</sub> = 25 °C; Fig. 3  |         | -   | 600 | A    |
| T <sub>stg</sub>            | storage temperature                          |  |         | -55 | 175 | °C   |
| T <sub>j</sub>              | junction temperature                         |  |         | -55 | 175 | °C   |
| <b>Source-drain diode</b>   |  |  |         |     |     |      |
| I <sub>S</sub>              | source current                               | T <sub>mb</sub> = 25 °C  | [2]     | -   | 145 | A    |
| I <sub>SM</sub>             | peak source current                          | pulsed; t <sub>p</sub> ≤ 10 μs; T <sub>mb</sub> = 25 °C  |         | -   | 600 | A    |
| <b>Avalanche ruggedness</b> |  |  |         |     |     |      |
| E <sub>DS(AL)S</sub>        | non-repetitive drain-source avalanche energy | I <sub>D</sub> = 190 A; V <sub>sup</sub> ≤ 40 V; R <sub>GS</sub> = 50 Ω; V <sub>GS</sub> = 10 V; T <sub>j(init)</sub> = 25 °C; unclamped; Fig. 4 | [3] [4] | -   | 154 | mJ   |

- [1] 190A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature
- [2] 145A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature
- [3] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.
- [4] Refer to application note AN10273 for further information.



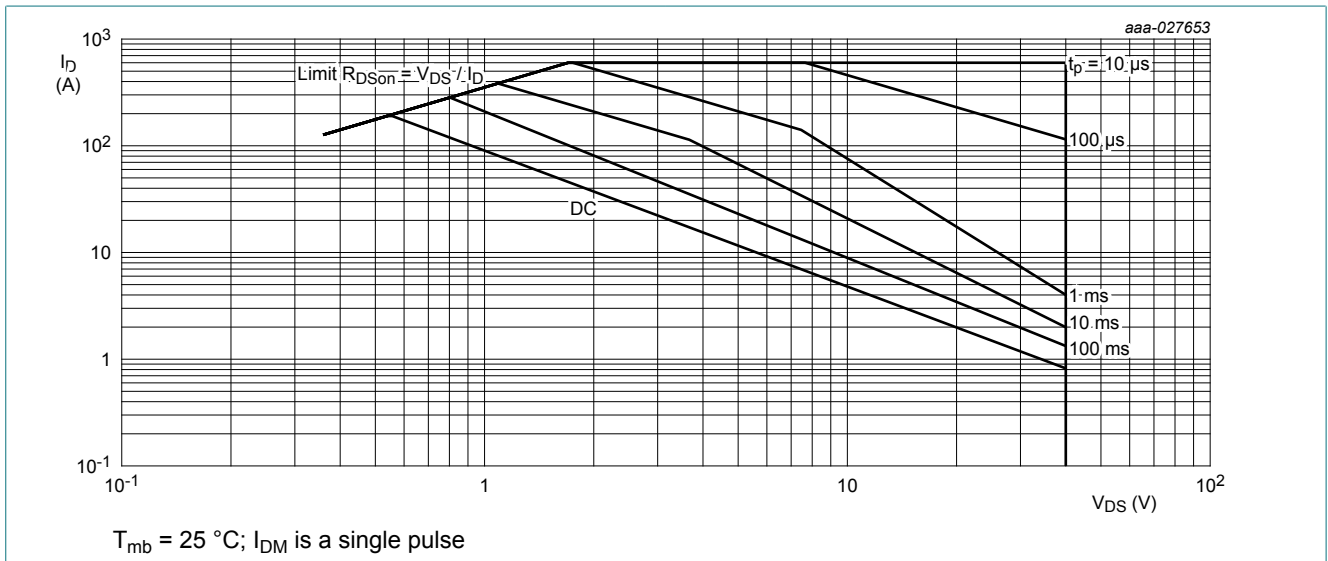


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

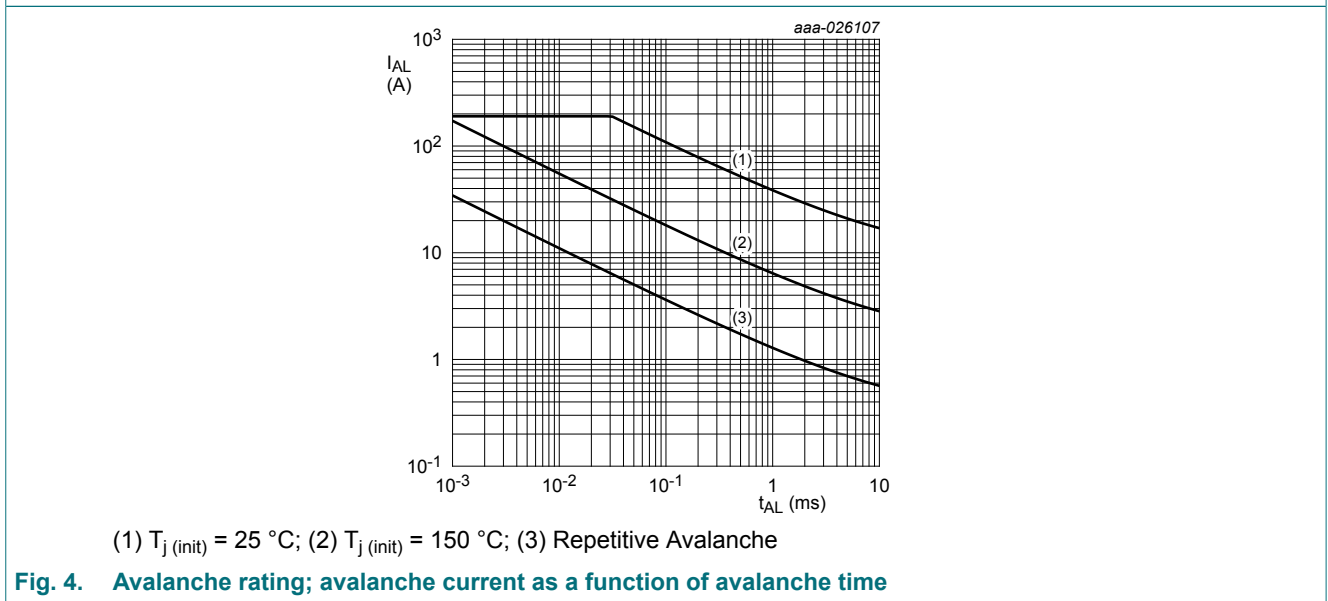
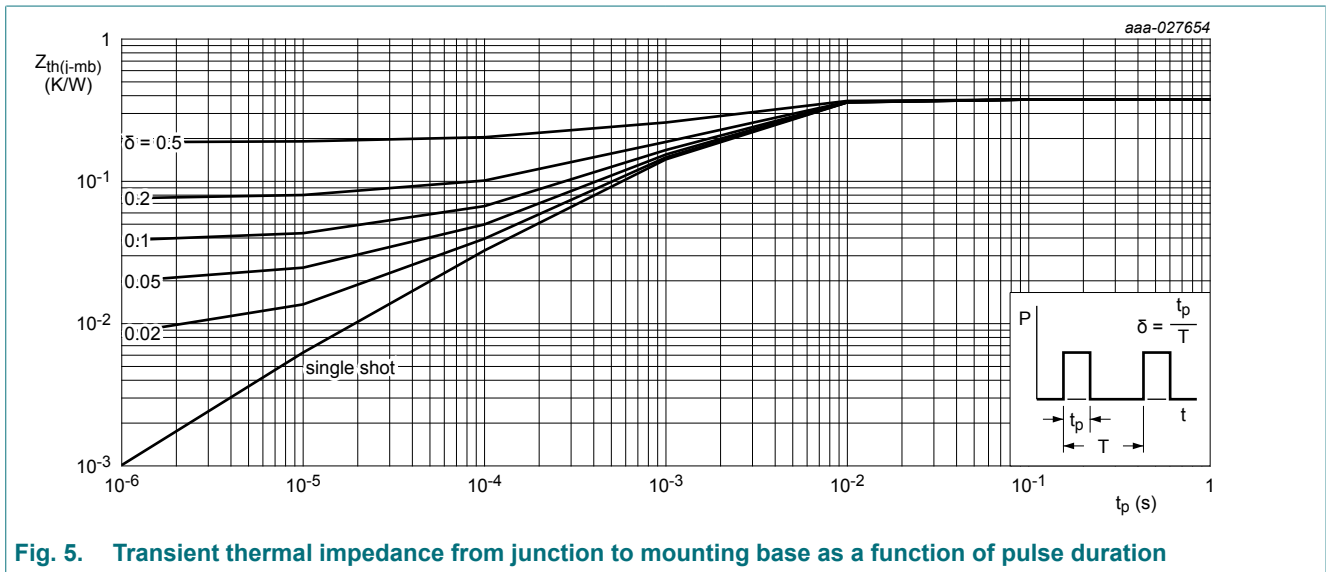


Fig. 4. Avalanche rating; avalanche current as a function of avalanche time

## 9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol         | Parameter   | Conditions             | Min | Typ  | Max  | Unit |
|----------------|---|------------------------|-----|------|------|------|
| $R_{th(j-mb)}$ | thermal resistance from junction to mounting base | <a href="#">Fig. 5</a> | -   | 0.29 | 0.38 | K/W  |



## 10. Characteristics

Table 7. Characteristics

| Symbol                        | Parameter                      | Conditions  | Min  | Typ  | Max  | Unit    |
|-------------------------------|--------------------------------|---|------|------|------|---------|
| <b>Static characteristics</b> |                                |   |      |      |      |         |
| $V_{(BR)DSS}$                 | drain-source breakdown voltage | $I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$                                      | 40   | 43   | -    | V       |
|                               |                                | $I_D = 250 \mu A; V_{GS} = 0 V; T_j = -40 \text{ }^\circ C$                                     | -    | 40.5 | -    | V       |
|                               |                                | $I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 \text{ }^\circ C$                                     | 36   | 40   | -    | V       |
| $V_{GS(th)}$                  | gate-source threshold voltage  | $I_D = 1 \text{ mA}; V_{DS}=V_{GS}; T_j = 25 \text{ }^\circ C; \text{ Fig. 9}; \text{ Fig. 10}$ | 1.35 | 1.62 | 2.05 | V       |
|                               |                                | $I_D = 1 \text{ mA}; V_{DS}=V_{GS}; T_j = 175 \text{ }^\circ C; \text{ Fig. 10}$                | 0.6  | -    | -    | V       |
|                               |                                | $I_D = 1 \text{ mA}; V_{DS}=V_{GS}; T_j = -55 \text{ }^\circ C; \text{ Fig. 10}$                | -    | -    | 2.5  | V       |
| $I_{DSS}$                     | drain leakage current          | $V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$                        | -    | 0.4  | 1    | $\mu A$ |
|                               |                                | $V_{DS} = 16 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ }^\circ C$                       | -    | 2.4  | 10   | $\mu A$ |
|                               |                                | $V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ }^\circ C$                       | -    | 0.34 | 1    | mA      |
| $I_{GSS}$                     | gate leakage current           | $V_{GS} = 16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$                        | -    | 2    | 100  | nA      |
|                               |                                | $V_{GS} = -10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$                       | -    | 2    | 100  | nA      |

## N-channel 40 V, 1.3 mΩ logic level MOSFET in LPAK56

| Symbol                         | Parameter                        | Conditions   | Min  | Typ  | Max  | Unit |
|--------------------------------|----------------------------------|--|------|------|------|------|
| R <sub>DSon</sub>              | drain-source on-state resistance | V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; <a href="#">Fig. 11</a>   | 0.67 | 0.96 | 1.3  | mΩ   |
|                                |                                  | V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 105 °C; <a href="#">Fig. 12</a>  | 1    | 1.47 | 2.1  | mΩ   |
|                                |                                  | V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 125 °C; <a href="#">Fig. 12</a>  | 1.1  | 1.6  | 2.3  | mΩ   |
|                                |                                  | V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 175 °C; <a href="#">Fig. 12</a>  | 1.4  | 2.04 | 2.8  | mΩ   |
|                                |                                  | V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; <a href="#">Fig. 11</a>  | 0.85 | 1.21 | 1.8  | mΩ   |
|                                |                                  | V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 105 °C; <a href="#">Fig. 12</a>   | 1.26 | 1.82 | 2.8  | mΩ   |
|                                |                                  | V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 125 °C; <a href="#">Fig. 12</a>   | 1.4  | 1.97 | 3.1  | mΩ   |
|                                |                                  | V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 175 °C; <a href="#">Fig. 12</a>   | 1.76 | 2.5  | 3.9  | mΩ   |
| R <sub>G</sub>                 | gate resistance                  | f = 1 MHz; T <sub>j</sub> = 25 °C  | 0.58 | 1.46 | 3.65 | mΩ   |
| <b>Dynamic characteristics</b> |                                  |  |      |      |      |      |
| Q <sub>G(tot)</sub>            | total gate charge                | I <sub>D</sub> = 25 A; V <sub>DS</sub> = 20 V; V <sub>GS</sub> = 10 V; <a href="#">Fig. 13</a> ; <a href="#">Fig. 14</a>                               | -    | 99   | 139  | nC   |
|                                |                                  | I <sub>D</sub> = 25 A; V <sub>DS</sub> = 20 V; V <sub>GS</sub> = 4.5 V; <a href="#">Fig. 13</a> ; <a href="#">Fig. 14</a>                              | -    | 45.3 | 63.4 | nC   |
| Q <sub>GS</sub>                | gate-source charge               |  | -    | 16.1 | 24.2 | nC   |
| Q <sub>GD</sub>                | gate-drain charge                |  | -    | 11.2 | 22.4 | nC   |
| C <sub>iss</sub>               | input capacitance                | V <sub>DS</sub> = 25 V; V <sub>GS</sub> = 0 V; f = 1 MHz; T <sub>j</sub> = 25 °C; <a href="#">Fig. 15</a>  | -    | 6978 | 9769 | pF   |
| C <sub>oss</sub>               | output capacitance               |  | -    | 1244 | 1742 | pF   |
| C <sub>rss</sub>               | reverse transfer capacitance     |  | -    | 269  | 592  | pF   |
| t <sub>d(on)</sub>             | turn-on delay time               | V <sub>DS</sub> = 20 V; R <sub>L</sub> = 0.8 Ω; V <sub>GS</sub> = 4.5 V; R <sub>G(ext)</sub> = 5 Ω   | -    | 36.3 | -    | ns   |
| t <sub>r</sub>                 | rise time                        |  | -    | 42.5 | -    | ns   |
| t <sub>d(off)</sub>            | turn-off delay time              |  | -    | 51.8 | -    | ns   |
| t <sub>f</sub>                 | fall time                        |  | -    | 30.7 | -    | ns   |
| <b>Source-drain diode</b>      |                                  |  |      |      |      |      |
| V <sub>SD</sub>                | source-drain voltage             | I <sub>S</sub> = 25 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C; <a href="#">Fig. 16</a>  | -    | 0.8  | 1.2  | V    |
| t <sub>rr</sub>                | reverse recovery time            | I <sub>S</sub> = 25 A; dI <sub>S</sub> /dt = -100 A/μs; V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 20 V; T <sub>j</sub> = 25 °C; <a href="#">Fig. 17</a> | -    | 38.7 | -    | ns   |
| Q <sub>r</sub>                 | recovered charge                 |  | -    | 38.8 | -    | nC   |
| S                              | softness factor                  |  | -    | 0.8  | -    |      |
|                                |                                  | I <sub>S</sub> = 25 A; dI <sub>S</sub> /dt = -500 A/μs; V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 20 V; T <sub>j</sub> = 25 °C; <a href="#">Fig. 17</a> | -    | 0.72 | -    |      |

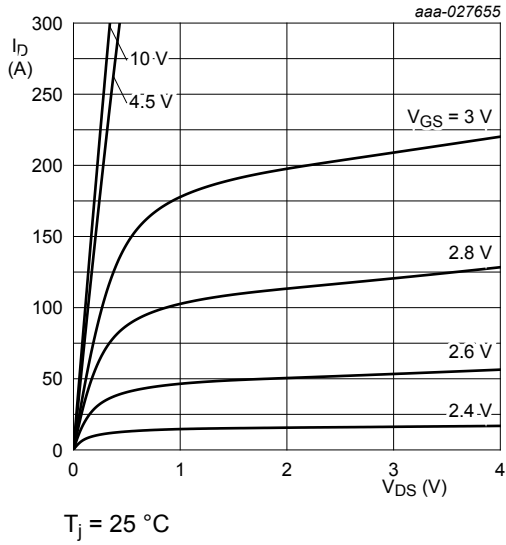


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

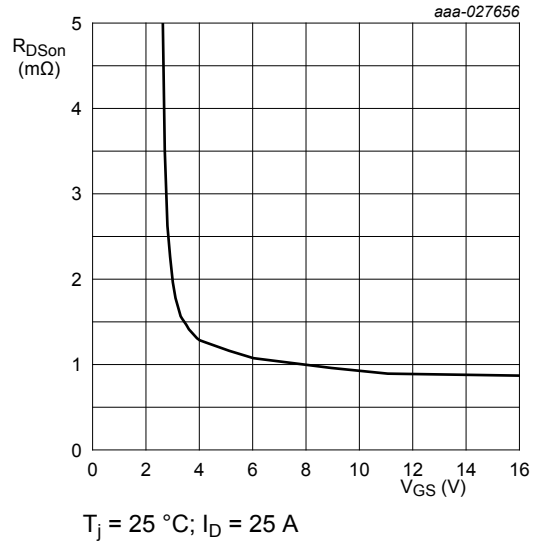


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

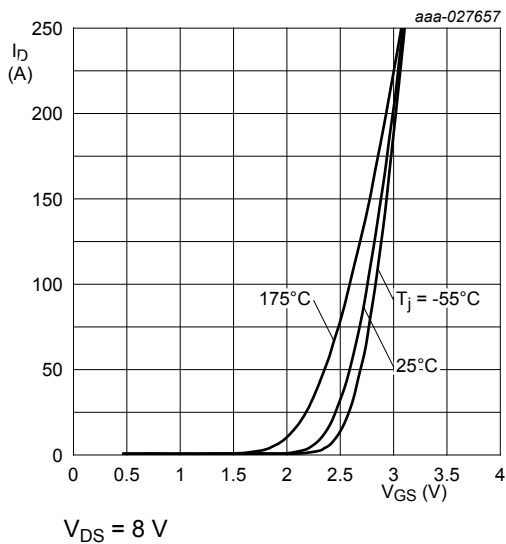


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values

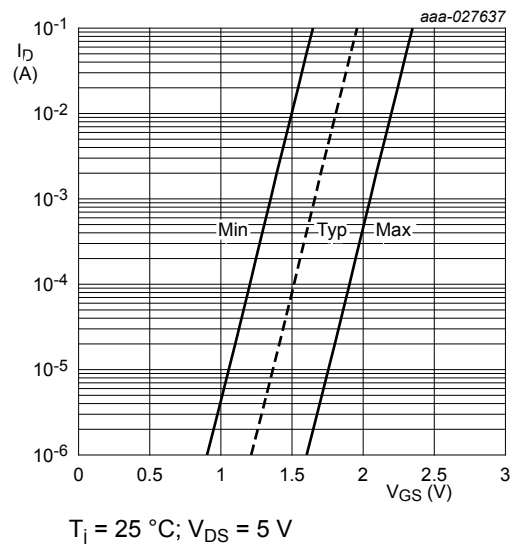
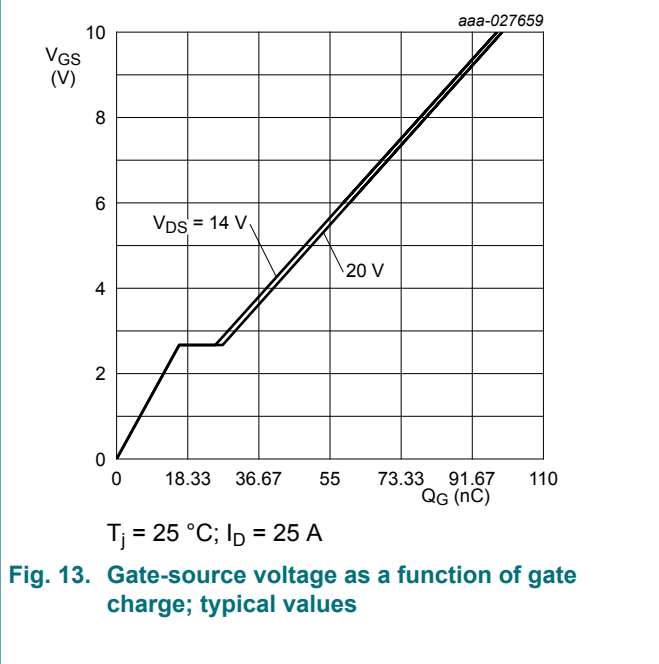
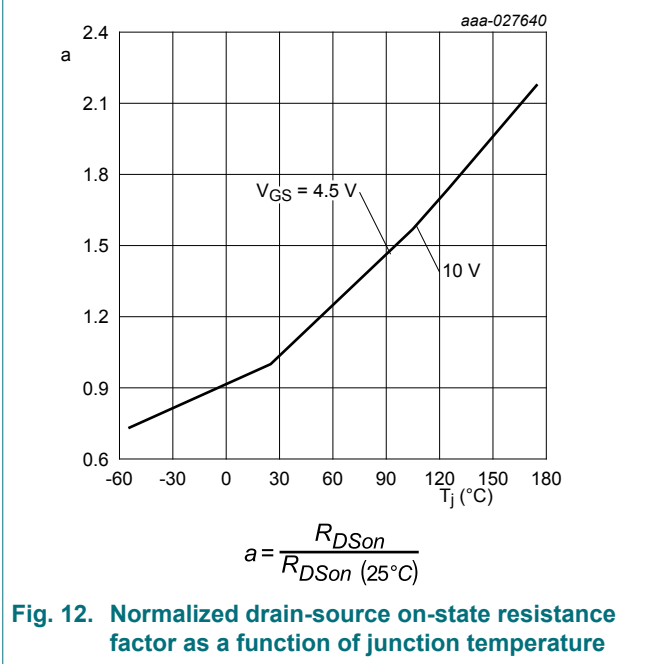
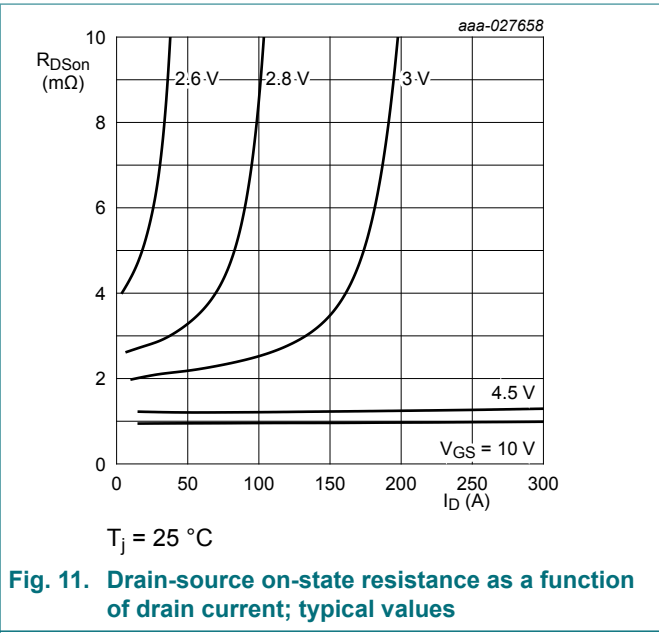
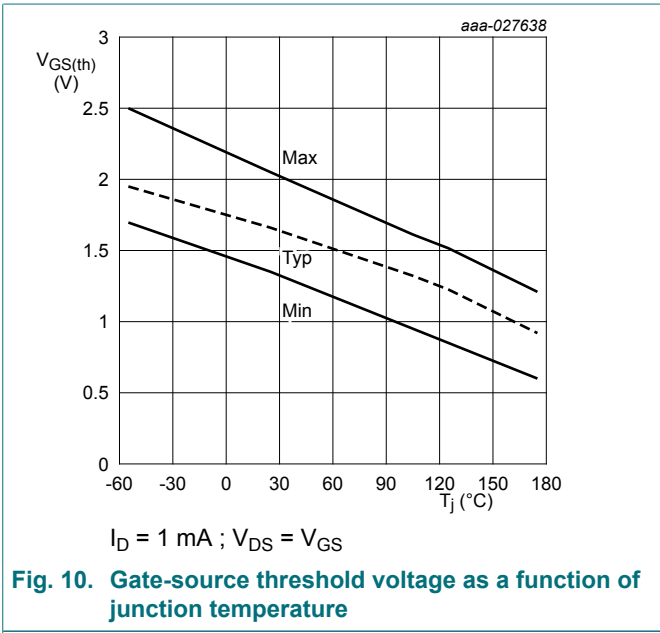
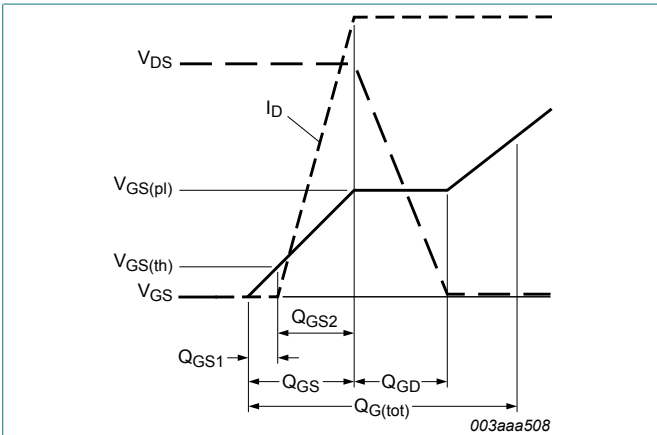


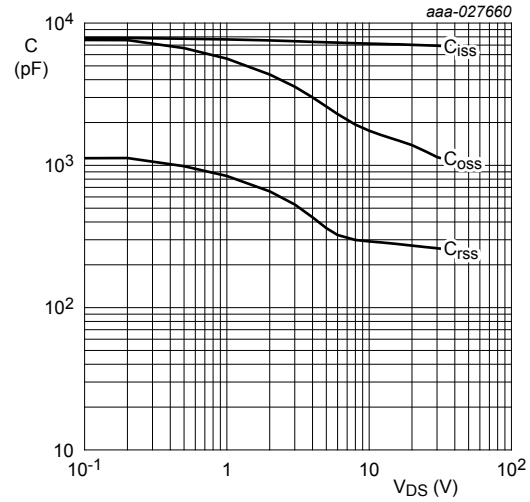
Fig. 9. Sub-threshold drain current as a function of gate-source voltage





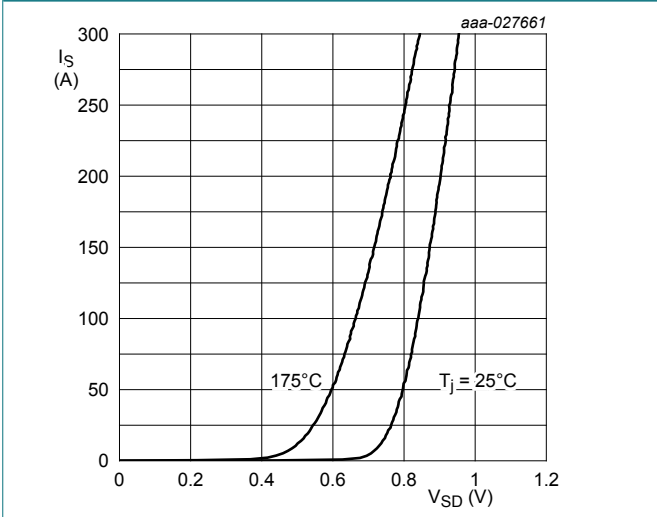


**Fig. 14. Gate charge waveform definitions**



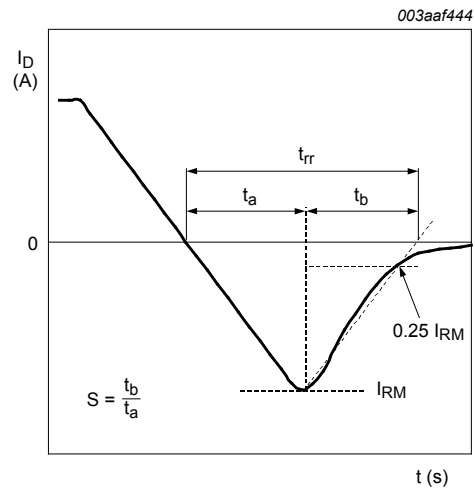
$V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$

**Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values**



$V_{GS} = 0 \text{ V}$

**Fig. 16. Source-drain (diode forward) current as a function of source-drain (diode forward) voltage; typical values**



$$t_{rr} = t_a + t_b$$

**Fig. 17. Reverse recovery waveform definitions**

### 11. Package outline

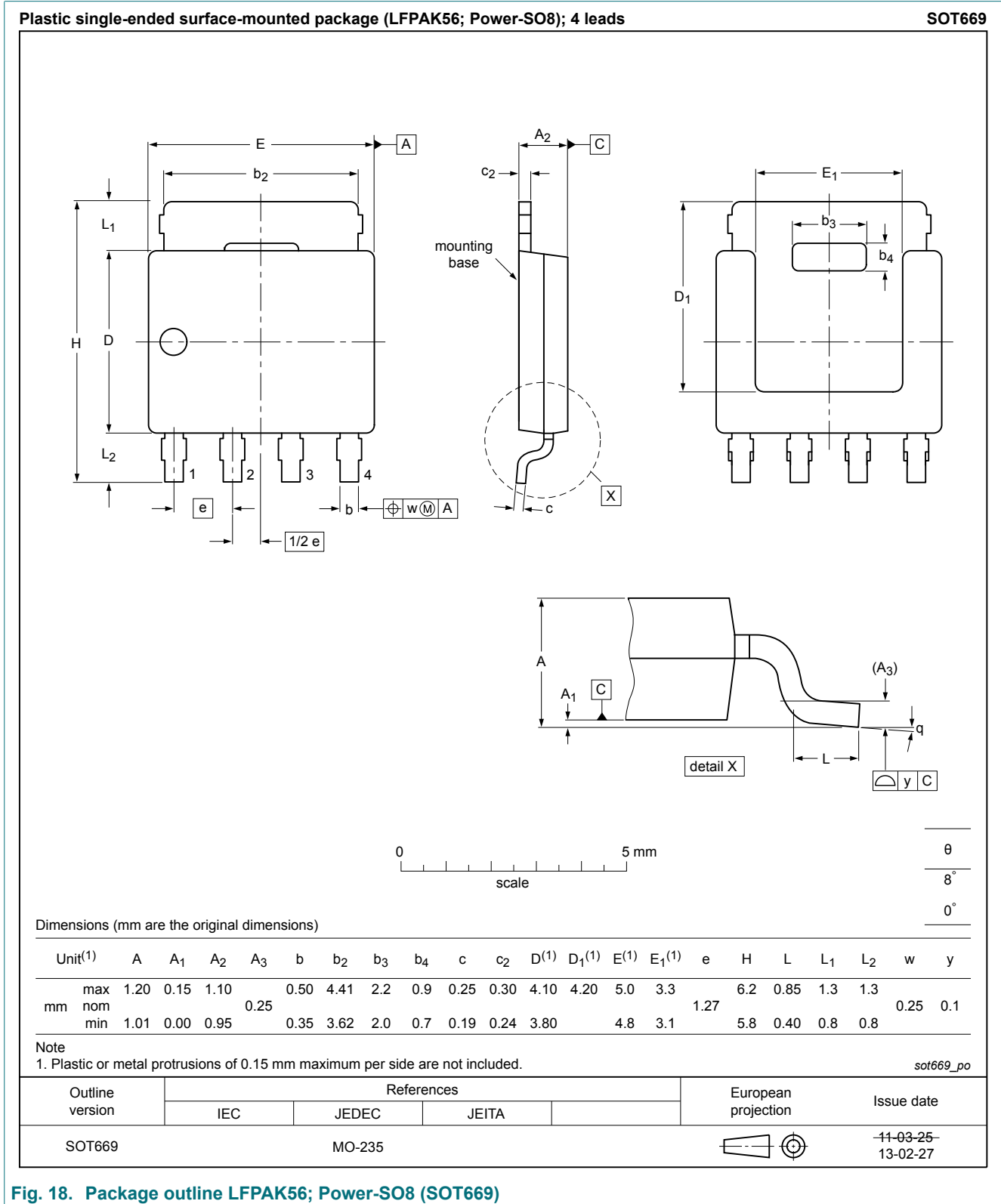


Fig. 18. Package outline LPAK56; Power-SO8 (SOT669)

## 12. Legal information

### Data sheet status

| Document status [1][2]         | Product status [3] | Definition  |
|--------------------------------|--------------------|---|
| Objective [short] data sheet   | Development        | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification      | This document contains data from the preliminary specification.                       |
| Product [short] data sheet     | Production         | This document contains the product specification.                                     |

- [1] Please consult the most recently issued document before initiating or completing a design.
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